HP83000 Model F660 Specifications

Channel Specifications Driver					
pulse performance at pin, measured					
into 50 0hms at coaxial connector:					
at level	ECL (-1.7V, -0.9V) CMOS (0.5V, 3.5V)				
transition times (20% to 80%) (typ.)	<250ps <350ps				
min. pulse width	0.75ns 1ns				
typical	0.6ns				
source impedance	50ohms±5%				
max. output current	>50mA				
output swing ¹	0.5V to 5V into open				
level range (low level/high level)	-2.5V to $+3V / -1.5V$ to $+5.5V$				
level resolution	10mV				
level accuracy (DC)	+(20mV + 0.1% of programmed level)				
high-Z compliance levels (I/O pins)	Vlow to (Vhigh + 500mV)				
data formats	600MHz mode 330MHz mode				
inputs (I) mode	DNRZ + High Z DNRZ + High Z				
	RZ+HighZ RZ+HighZ				
	R1+HighZ R1+HighZ				
	RC+HighZ RC+HighZ				
bidirectional (I/O) mode	- $DNRZ \pm High Z$				
Channel Specifications Comparator					
threshold range (single threshold,					
prog. per pin)	-2.5V to 5.5V				
threshold resolution	10mV				
threshold accuracy	$\pm (20 \text{mV} + 0.1\% \text{ of programmed value})$				
min. detectable pulse width	300ps				
min. overdrive	10% of programmed amplitude, min. 150mV				
impedance					
terminated by corresponding driver	50 ohms($ r \le 10\%$ at $t_r \ge 250 ps$) ²				
high-Z	10 κ Ω parallel with 15pF (lumped)				
compare modes	660MHz mode 330MHz mode				
output (O) mode	edge, window edge, window				
bidirectional (I/O) mode	- edge				
¹ programmable down to 0V.	2 Where: r = reflection coefficient				
	$t_r = rise time$				
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Timing Specifications				
timing measurement accuracy ³				
edge placement accuracy ⁴ :	± 50ps			
Driver	± 80ps			
Receiver	± 80ps			
edge placement resolution	10ps			
edge placement range:				
driver leading edge (DLE)	-4 to $+12$ periods, (within -100 ns to $+500$ ns)			
driver trailing (DTE)	DLE +0.50ns to DLE + period -0.50ns, (within -100ns to +500ns)			
comparator leading edge (CLE)	-4 to $+12$ periods, (within -100 ns to $+500$ ns)			
comparator trailing edge (CTE)	CLE + 0.75ns to $CLE + period - 0.75$ ns, (within -100 ns to $+500$ ns)			
high-Z to active edge				
placement accuracy	1ns			
vector period	660MHz mode 330Mhz mode			
range	1.50ns to 500ns 3.00ns to 500ns			
accuracy	$\pm 0.1\%$ of period			
resolution	3 digits			
external clock				
period range	750ps to 500ps			
synchronization	period = $n*$ external clock period ($n = 1,2,4,8$)			
DC Parametria Magaurement Unit Specifications				

DC Parametric Measurement Unit Specifications

1 PMU per I/O board (16 channels), switchable to each channel within one I/O board.

operating modes:	— measure voltage	— force voltage / measure current		
	— measure curren	t — forc	— force current / measure voltage	
Mode	Range	Resolution	Accuracy ⁵	
voltage force	$\pm 10V$	$5 \text{ mV} \pm 0.5\%$	± 20 mV-(Ia* R)	
	$\pm 2V$	1 mV	$\pm 0.5\% \pm 4$ mV-($Ia*R$)	
voltage measure	±10 V	5 mV	$\pm 0.3\% \pm 10$ mV-(Ia*R)	
	$\pm 2V$	1 mV	$\pm 0.3\% \pm 3$ mV-(Ia*R)	
currentforce	±200mA	100μΑ	±0.5% ±1mA	
	$\pm 20 \text{mA}$	10μΑ	$\pm 0.5\% \pm 100 \mu A$	
	$\pm 2mA$	1μA	$\pm 0.5\%$ $\pm 10 \mu A$	
	$\pm 200 \mu A$	100nA	$\pm 0.5\%$ $\pm 1 \mu A$	
	$\pm 20 \mu A$	l0nA	±0.5% ±100nA	
	$\pm 2\mu A$	1nA	±0.5% ±20nA	
current measure	$\pm 200 \text{mA}$	100μΑ	$\pm 0.5\% \pm 1 \text{ mA}$	
	$\pm 20 \text{mA}$	10μΑ	$\pm 0.5\% \pm 100 \mu A$	
	±2mA	1mA	$\pm 0.5\% \pm 10 \mu A$	
	$\pm 200 \mu A$	100nA	$\pm 0.5\% \pm 1 \mu A$	
	±20µA	10nA	±0.5% ±100nA	
	±2µA	1nA	±0.5% ±20nA	
³ For setup, hold and proposetion delay. ⁴ Valid for all pins at all settings and conditions				

³For setup, hold and propagation-delay measurements after reference measurement. Timing formats for pin under test must be DNRZ/Edge Compare. Timing can be varied for one pin at a time at stable settings and temperature.

⁴Valid for all pins at all settings and conditions at all calibrated frequencies and levels. ⁵Accuracy specifications are given as % of programmed or measured value Ia = actual current. R = wiring resistance; (see

DUT interface types).